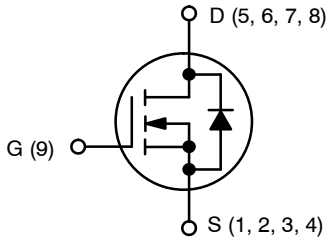
MOSFET – Power, Single N-Channel, Source-Down TDFN9
60 V, 1.3 mΩ, 243 A

NTMFSS1D3N06CL

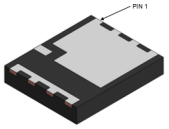
$V_{(BR)DSS}$	$R_{DS(ON)}$ MAX	I_D MAX
60 V	1.3 mΩ @ 10 V	243 A
	2.0 mΩ @ 4.5 V	



N–CHANNEL MOSFET

Features
- Small Footprint (5x6 mm) for Compact Design
- Low $R_{DS(on)}$ to Minimize Conduction Losses
- Low Q_G and Capacitance to Minimize Driver Losses
- These Devices are Pb–Free, Halogen–Free / BFR Free and are RoHS Compliant

Typical Applications
- DC–DC Converters
- Power Load Switch
- Notebook Battery Management
- Synchronous Rectifier



TDFN9 5x6
CASE 520AE

MARKING DIAGRAM

XXXX = Specific Device Code
A = Assembly Location
Y = Year
W = Work Week
ZZ = Wafer Lot

MAXIMUM RATINGS (T_J = 25°C unless otherwise noted)

Parameter			Symbol	Value	Unit
Drain–to–Source Voltage			V_{DSS}	60	V
Gate–to–Source Voltage			V_{GS}	±20	V
Continuous Drain Current $R_{\theta JC}$	Steady State	T_C = 25°C	I_D	243	A
		T_C = 100°C		153	
Power Dissipation $R_{\theta JC}$	Steady State	T_C = 25°C	P_D	153	W
		T_C = 100°C		61	
Continuous Drain Current $R_{\theta JA}$ (Notes 1, 2)	Steady State	T_A = 25°C	I_D	31	A
		T_C = 100°C		19	
Power Dissipation $R_{\theta JA}$ (Notes 1, 2)		T_A = 25°C	P_D	2.5	W
		T_C = 100°C		1	
Pulsed Drain Current	T_A = 25°C, t_p = 10 μs		I_{DM}	1758	A
Operating Junction and Storage Temperature Range			T_J, T_{stg}	–55 to +150	°C
Single Pulse Drain–to–Source Avalanche Energy ($I_{L(pk)}$ = 79 A)			E_{AS}	234	mJ
Lead Temperature Soldering Reflow for Soldering Purposes (1/8″ from case for 10 s)			T_L	260	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

THERMAL RESISTANCE MAXIMUM RATINGS

Parameter	Symbol	Value	Unit
Junction–to–Case – Steady State	$R_{\theta JC}$	0.81	°C/W
Junction–to–Ambient – Steady State (Note 2)	$R_{\theta JA}$	50	

1. The entire application environment impacts the thermal resistance values shown, they are not constants and are only valid for the particular conditions noted.
2. Surface–mounted on FR4 board using a 1 in^2 pad size, 2 oz. Cu pad.

ORDERING INFORMATION

Device	Package	Shipping†
NTMFSS1D3N06CL	TDFN9 (Pb–Free)	3000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

ELECTRICAL CHARACTERISTICS (T_J = 25°C unless otherwise specified)

Parameter	Symbol	Test Condition		Min	Typ	Max	Unit
OFF CHARACTERISTICS							
Drain−to−Source Breakdown Voltage	$V_{(BR)DSS}$	V_{GS} = 0 V, I_D = 250 μA		60			V
Drain−to−Source Breakdown Voltage Temperature Coefficient	$V_{(BR)DSS}/T_J$	I_D = 250 μA, ref to 25°C			24		mV/°C
Zero Gate Voltage Drain Current	I_{DSS}	V_{GS} = 0 V, V_{DS} = 60 V	T_J = 25°C			10	μA
Gate−to−Source Leakage Current	I_{GSS}	V_{DS} = 0 V, V_{GS} = 20 V				100	nA
ON CHARACTERISTICS							
Gate Threshold Voltage	$V_{GS(TH)}$	V_{GS} = V_{DS}, I_D = 250 μA		1.2		2.0	V
Threshold Temperature Coefficient	$V_{GS(TH)}/T_J$	I_D = 250 μA, ref to 25°C			−5.9		mV/°C
Drain−to−Source On Resistance	$R_{DS(on)}$	V_{GS} = 10 V, I_D = 50 A			1.0	1.3	mΩ
		V_{GS} = 4.5 V, I_D = 50 A			1.3	2.0	
Forward Transconductance	g_{FS}	V_{DS} = 15 V, I_D = 50 A			180		S
Gate Resistance	R_G	T_A = 25°C			0.6		Ω
CHARGES & CAPACITANCES							
Input Capacitance	C_{ISS}	V_{GS} = 0 V, f = 1 MHz, V_{DS} = 30 V			8190		pF
Output Capacitance	C_{OSS}				3950		
Reverse Capacitance	C_{RSS}				25		
Total Gate Charge	$Q_{G(TOT)}$	V_{GS} = 10 V, V_{DS} = 30 V, I_D = 50 A			117		nC
Total Gate Charge	$Q_{G(TOT)}$	V_{GS} = 4.5 V, V_{DS} = 30 V, I_D = 50 A			53		
Gate−to−Drain Charge	Q_{GD}				10		
Gate−to−Source Charge	Q_{GS}				22.4		
Plateau Voltage	V_{GP}				2.8		V
SWITCHING CHARACTERISTICS (Note 3)							
Turn−On Delay Time	$t_{d(ON)}$	V_{GS} = 4.5 V, V_{DD} = 30 V, I_D = 50 A, R_G = 2.5 Ω			19.6		ns
Rise Time	t_r				9.2		
Turn−Off Delay Time	$t_{d(OFF)}$				55		
Fall Time	t_f				14		
SOURCE−TO−DRAIN DIODE CHARACTERISTICS							
Forward Diode Voltage	V_{SD}	V_{GS} = 0 V, I_S = 50 A	T_J = 25°C		0.79	1.2	V
			T_J = 125°C		0.65		
Reverse Recovery Time	t_{RR}	V_{GS} = 0 V, dI/dt = 100 A/μs, I_S = 50 A			84		ns
Charge Time	t_a				43		
Discharge Time	t_b				41		
Reverse Recovery Charge	Q_{RR}				153		nC

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

3. Switching characteristics are independent of operating junction temperatures.

TYPICAL CHARACTERISTICS

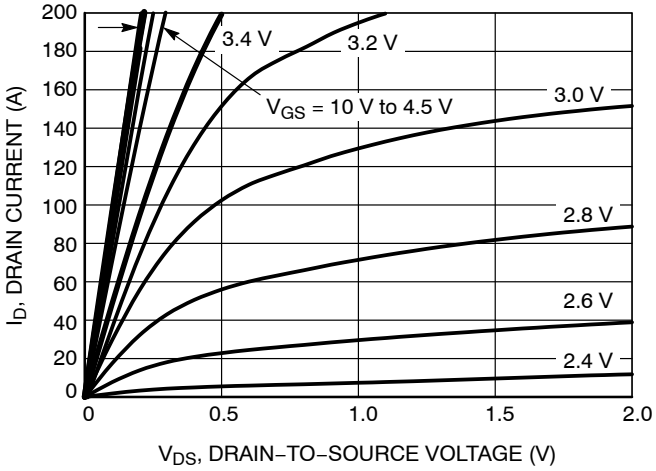


Figure 1. On−Region Characteristics

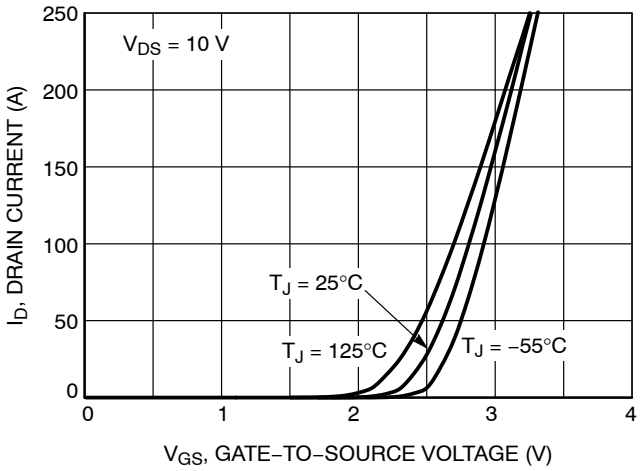


Figure 2. Transfer Characteristics

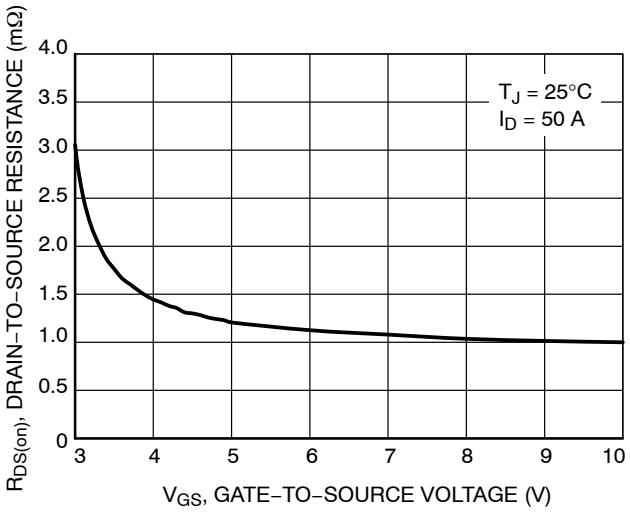


Figure 3. On−Resistance vs. Gate−to−Source Voltage

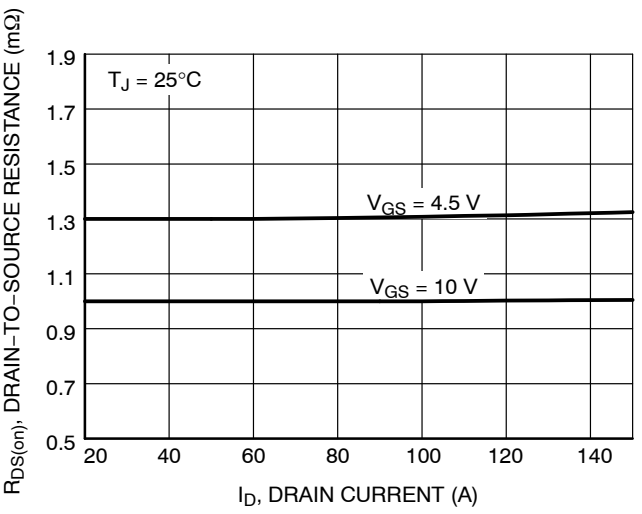


Figure 4. On−Resistance vs. Drain Current and Gate Voltage

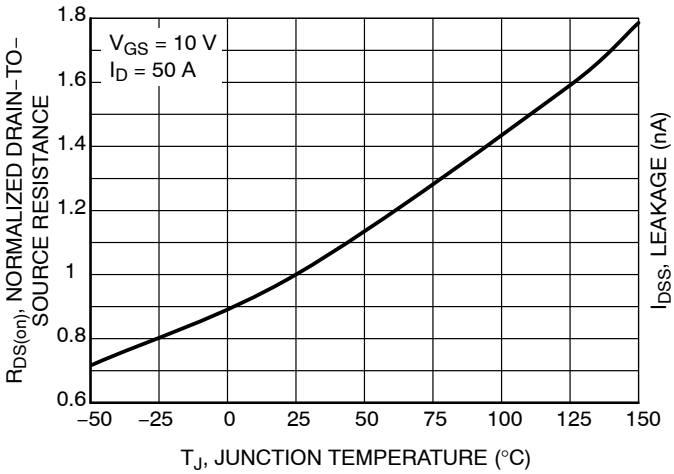


Figure 5. On−Resistance Variation with Temperature

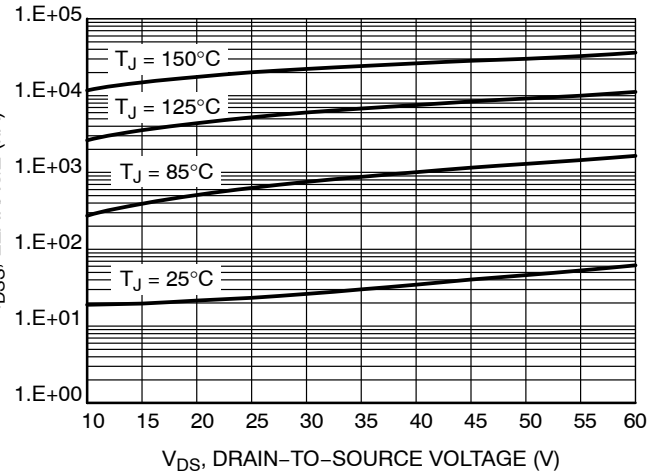


Figure 6. Drain−to−Source Leakage Current vs. Voltage

TYPICAL CHARACTERISTICS

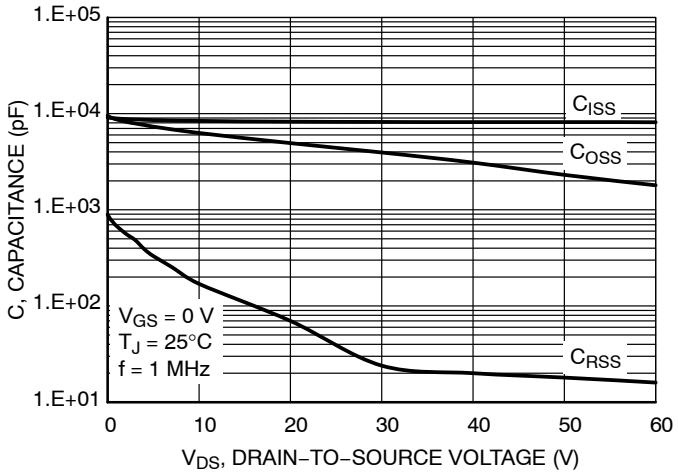


Figure 7. Capacitance Variation

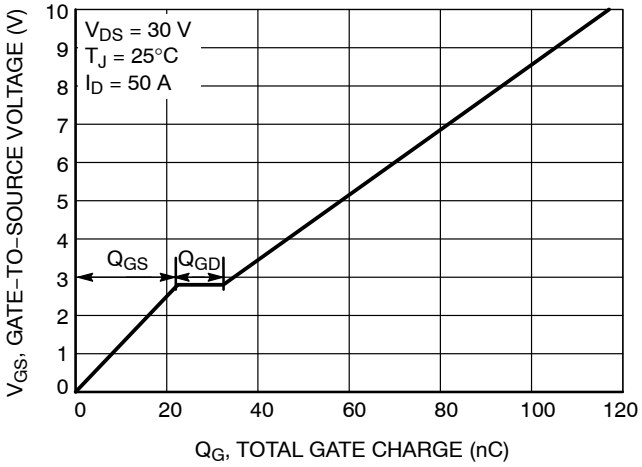


Figure 8. Gate−to−Source vs. Total Charge

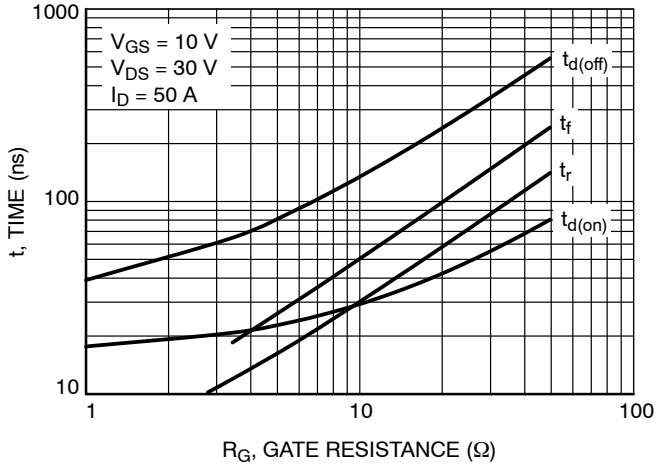


Figure 9. Resistive Switching Time Variation vs. Gate Resistance

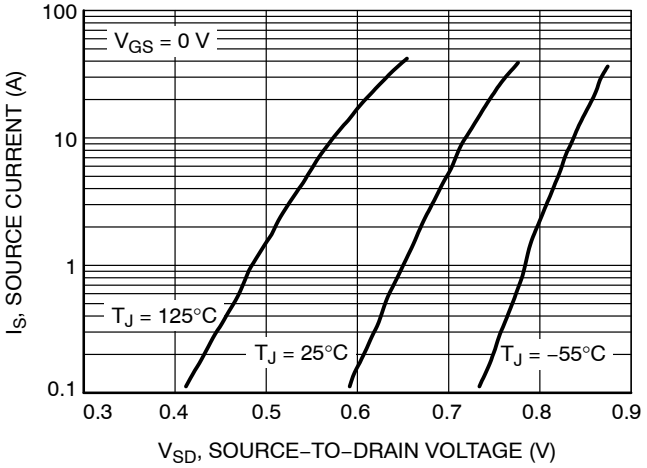


Figure 10. Diode Forward Voltage vs. Current

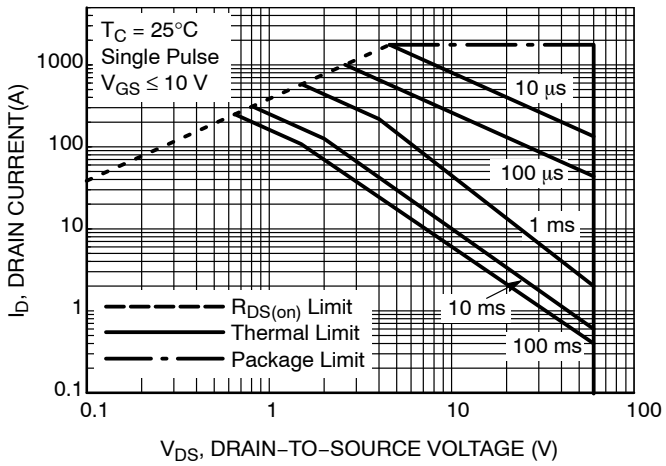


Figure 11. Safe Operating Area

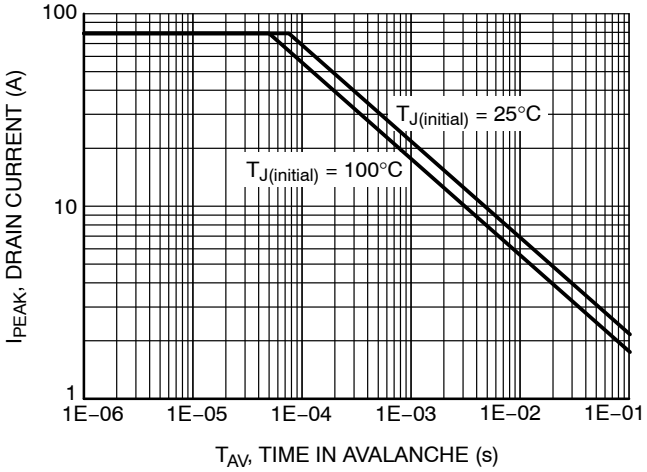


Figure 12. I_{PEAK} vs. Time in Avalanche

TYPICAL CHARACTERISTICS

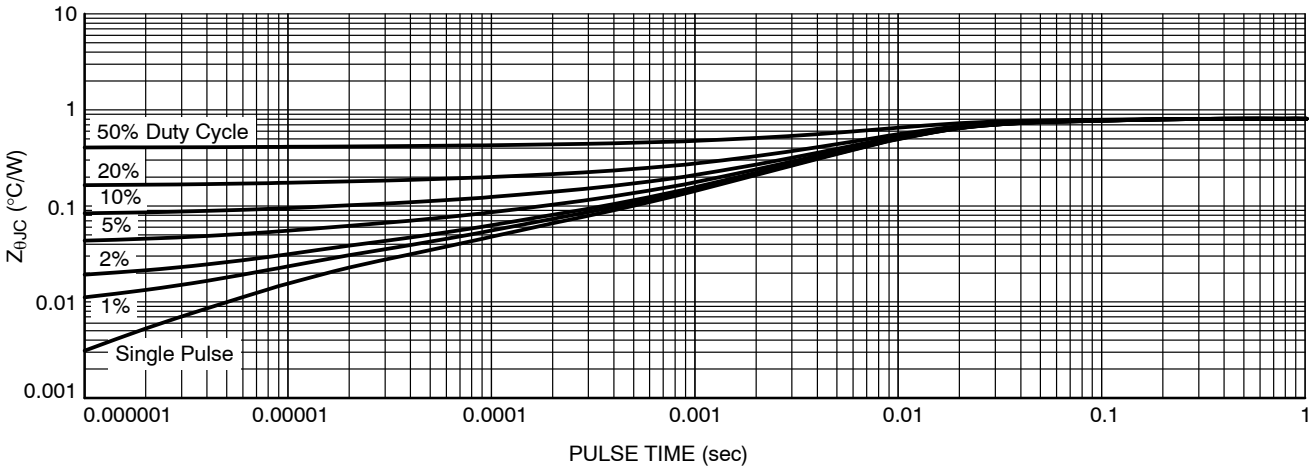
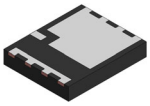


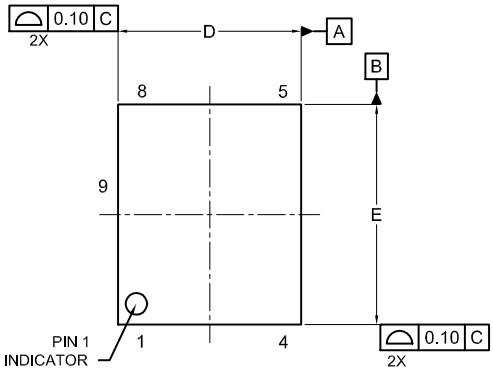
Figure 13. Thermal Characteristics

MECHANICAL CASE OUTLINE
PACKAGE DIMENSIONS

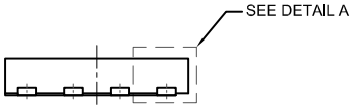


TDFN9 5x6, 1.27P
CASE 520AE
ISSUE B

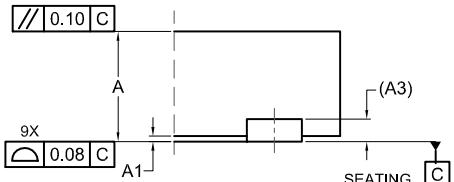
DATE 24 NOV 2022



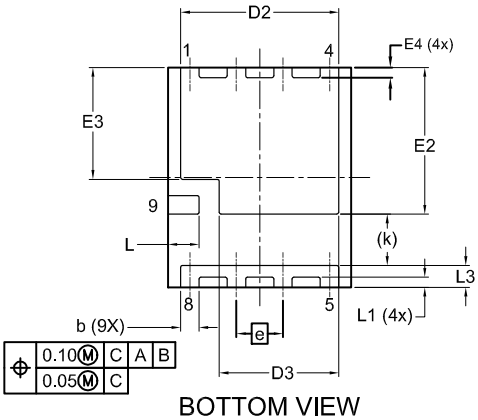
TOP VIEW



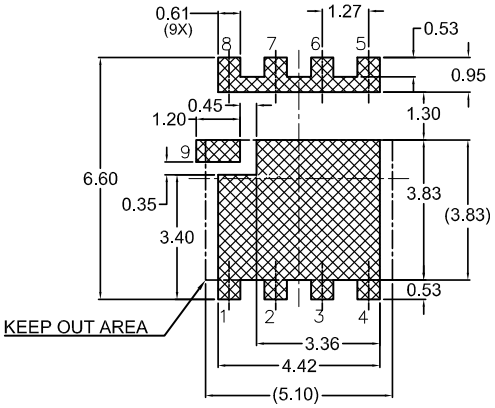
FRONT VIEW



DETAIL A
SCALE: 3:1



BOTTOM VIEW



LAND PATTERN
RECOMMENDATION

*FOR ADDITIONAL INFORMATION ON OUR PB-FREE STRATEGY AND SOLDERING DETAILS, PLEASE DOWNLOAD THE ON SEMICONDUCTOR SOLDERING AND MOUNTING TECHNIQUES REFERENCE MANUAL, SOLDERRM/D.

NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2009.
2. CONTROLLING DIMENSION: MILLIMETERS
3. COPLANARITY APPLIES TO THE EXPOSED PADS AS WELL AS THE TERMINALS.
4. DIMENSIONS D1, D2, E1 AND E2 DO NOT INCLUDE MOLD FLASH.
5. SEATING PLANE IS DEFINED BY THE TERMINALS. "A1" IS DEFINED AS THE DISTANCE FROM THE SEATING PLANE TO THE LOWEST POINT ON THE PACKAGE BODY.

DIM	MILLIMETERS		
	MIN	NOM	MAX
A	0.95	1.00	1.05
A1	0.00	0.02	0.05
A3		0.20 REF	
b	0.45	0.50	0.55
D	4.90	5.00	5.10
D2	4.10	4.30	4.50
D3	3.16	3.26	3.36
E	5.90	6.00	6.10
E2	3.90	4.00	4.10
E3	2.95	3.05	3.15
E4	0.18	0.28	0.38
e		1.27 BSC	
k		1.40 REF	
L	0.75	0.85	0.95
L1	0.18	0.28	0.38
L3	0.50	0.60	0.70

GENERIC MARKING DIAGRAM*

XXXX = Specific Device Code
A = Assembly Location
WL = Wafer Lot
Y = Year Code
WW = Work Week Code

*This information is generic. Please refer to device data sheet for actual part marking. Pb−Free indicator, “G” or microdot “▪”, may or may not be present. Some products may not follow the Generic Marking.

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DESCRIPTION:	**TDFN9 5x6, 1.27P**	**PAGE 1 OF 1**

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